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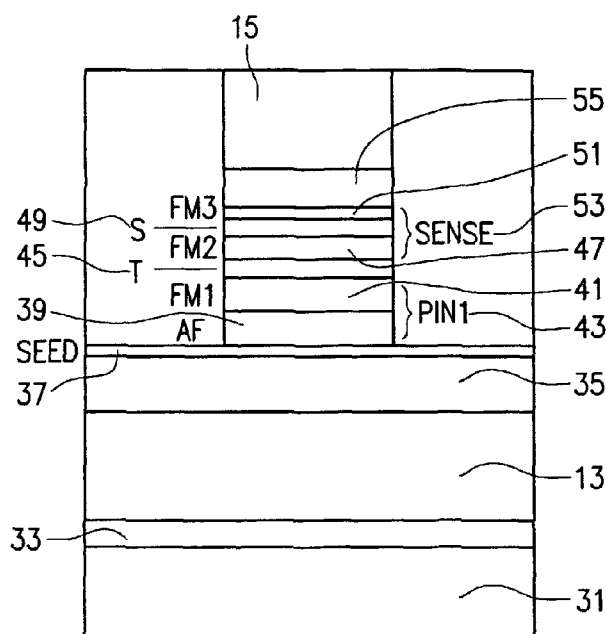
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(54) Title: **SYNTHETIC-FERRIMAGNET SENSE-LAYER FOR HIGH DENSITY MRAM APPLICATIONS**



(57) Abstract: An improved magnetic memory element is provided in which a magnetic sense layer is formed of two ferromagnetic material layers separated by a spacer layer. The two ferromagnetic layers are formed as a synthetic ferrimagnet with stray field coupling and antiferromagnetic exchange coupling across the spacer layer.



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